

General Description

The MAX1894/MAX1924 are lithium-ion/lithium-polymer (Li+) battery-pack protector ICs for 3- or 4-series Li+ battery packs. The MAX1894/MAX1924 enhance the useful operating life of Li+ batteries by monitoring individual cell voltages and preventing over/undervoltage conditions. The MAX1894/MAX1924 also protect the battery pack against charge current, discharge current, and packshort fault conditions.

In case of a fault condition, on-board drivers control external P-channel MOSFETs, which disconnect the cells from the pack external terminals. The external protection MOSFETs are connected in a common-source configuration that does not require external pullup resistors. The MAX1894/MAX1924 use only one current-sense resistor to achieve the protection features. All protection thresholds and delays do not require any external components and are trimmed at the factory.

If any cell voltage drops below the undervoltage threshold, the MAX1894/MAX1924 disconnect the pack from the load and power down to prevent deep discharge of the pack. The MAX1894/MAX1924 offer a trickle-charge feature, which provides a low-current path to safely charge a deeply discharged pack. The MAX1894/ MAX1924 also have two logic-level inputs, which can be used by a microcontroller to disable the protection MOSFETs and to put the device in shutdown. The MAX1894/MAX1924 have low quiescent current (30µA typ) and ultra-low shutdown current (0.8µA typ) to prevent deep-cell discharge.

The MAX1894X is designed for 4-series battery packs, without hysteresis on the protection thresholds. The MAX1924V and MAX1924X include hysteresis for the 3and 4-series packs, respectively.

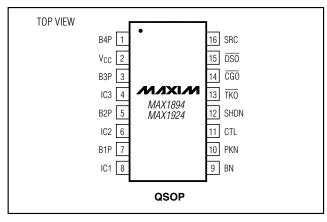
Applications

3- or 4-Series Li+ Battery Packs

Features

- ◆ Protect Against Cell Overvoltage Factory Programmable Limits from 4V to 4.4V Accurate to ±0.5%
- ♦ Protect Against Cell Undervoltage Factory Programmable Limits from 2V to 3.2V Accurate to ±2.0%
- ♦ Protect Against Charge, Discharge, and Pack-**Short Current Faults**
- ♦ Automatically Trickle Charges Deeply Discharged Cells
- ♦ Fully Integrated MOSFET Drivers Do Not Require **Pullup Resistors**
- ♦ 0.8µA (typ) Shutdown Supply Current Prevents **Deep Discharge of Cells**
- ♦ 30µA (typ) Operating Supply Current
- ♦ 28V (max) Input Voltage
- ♦ Available in Small 16-Pin QSOP Package

Pin Configuration



Ordering Information

| PART | TEMP RANGE | PIN-PACKAGE | CELLS | OVERVOLTAGE | OVERVOLTAGE THRESHOLD HYSTERESIS |
|-------------|----------------|-------------|-------|-------------|-------------------------------------|
| MAX1894XEEE | -40°C to +85°C | 16 QSOP | 4 | 4.25V* | No |
| MAX1924VEEE | -40°C to +85°C | 16 QSOP | 3 | 4.35V* | Yes |
| MAX1924XEEE | -40°C to +85°C | 16 QSOP | 4 | 4.35V* | Yes |

^{*}Contact factory for alternative threshold voltages.

Typical Applications Circuits appear at end of data sheet.

NIXIN

ABSOLUTE MAXIMUM RATINGS

| SRC, IC2, IC3, V _{CC} to BNIC1 to BN | | PKN to BN ESD Protection on |
|---|-------------|--------------------------------|
| DSO, TKO, CGO to BN | | Continuous Power |
| B4P to B3P | 0.3V to +6V | 16-Pin QSOP (d |
| B3P to B2P | 0.3V to +6V | Operating Temper |
| B2P to B1P | 0.3V to +6V | Junction Temperat |
| B1P to BN | 0.3V to +6V | Storage Temperati |
| CTL. SHDN to PKN | 0.3V to +6V | Lead Temperature |

| PKN to BN | 2V to +2V |
|---|----------------|
| ESD Protection on All Pins | ±2000V |
| Continuous Power Dissipation ($T_A = +70^{\circ}C$) | |
| 16-Pin QSOP (derate 8.3mW/°C above +70° | °C)667mW |
| Operating Temperature Range | 40°C to +85°C |
| Junction Temperature | +150°C |
| Storage Temperature Range | 65°C to +150°C |
| Lead Temperature (soldering, 10s) | +300°C |

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{SRC} = V_{B4P} + 0.1V$, each battery cell voltage $(V_{CELL}) = 3.6V$, $V_{CTL} = V_{SHDN} = V_{PKN}$, $T_A = 0^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | TYP | MAX | UNITS | |
|--|----------------------|---|-------|-------|-------|---------|--|
| SRC Input Current | | $V_{SRC} - V_{B_P} = 1V$ | | 20 | 40 | μΑ | |
| Supply Current (Note 1) | I _{SUP} | No faults | | 30 | 45 | μΑ | |
| Shutdown Supply Current | ISHDN | Undervoltage without charge source | | 0.8 | 2 | μΑ | |
| Top Cell Sampling Current (Note 2) | | V _{CELL} = 3.6V | | 60 | | μΑ | |
| Intermediate Cell Input Bias Current (Note 3) | | V _{CELL} = 3.6V | | 500 | | рА | |
| V _{CC} Undervoltage Lockout Threshold | | Rising edge, hysteresis = 1% falling edge | | 4.5 | | V | |
| Charge-Mode Detection Threshold | | VSRC - VB4P | 25 | | 100 | mV | |
| Overvelte se Threeheld (Nets 4) | \/ | MAX1894X cell voltage rising | 4.225 | 4.250 | 4.275 | 4.275 V | |
| Overvoltage Threshold (Note 4) | Vov_th | MAX1924X, MAX1924V cell voltage rising | | 4.350 | 4.375 | V | |
| Overvoltage Threshold Hysteresis | V _{OV_HYT} | MAX1924X, MAX1924V cell voltage falling | | 200 | | mV | |
| Undervoltage Threshold (Note 4) | V _{UV_TH} | Cell voltage falling | 2.260 | 2.300 | 2.340 | V | |
| PKN to BN Discharge Current Fault Threshold | V _{OD_TH} | | 130 | 145 | 160 | mV | |
| PKN to BN Charge Current Fault Threshold | V _{OC_TH} | | -120 | -100 | -80 | mV | |
| PKN to BN Discharge Current Fault Threshold, Pack-Short Condition | V _{PS_TH} | | 385 | 405 | 425 | mV | |
| Discharge or Charge Current Fault to DSO, CGO, TKO Transition Delay Time | t _{I-DELAY} | | 2.5 | 3 | 3.5 | ms | |
| Discharge Current Fault to DSO Transition Time Delay for Pack- Short Condition | tp-delay | | 400 | 450 | 500 | μs | |

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{SRC} = V_{B4P} + 0.1V$, each battery cell voltage $(V_{CELL}) = 3.6V$, $V_{CTL} = V_{SHDN} = V_{PKN}$, $T_A = 0^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.)

| PARAMETER | SYMBOL | CONDITIONS | MIN | TYP | MAX | UNITS |
|--|----------|--|-----|------|-----|-------|
| Charge-Voltage Comparator Threshold for Resetting Discharge-Current Fault Latch | | V _{SRC} - V _{B4P} | 25 | | 100 | mV |
| Discharge-Voltage Comparator Threshold for Resetting Charge- Current Fault Latch | | V _{B4P} - V _{SRC} | 25 | | 100 | mV |
| DSO, CGO, and TKO Sink Current | | V _{SRC} = 12V, V _{PIN} = 5V (Note 5) | 100 | 200 | | μΑ |
| DSO, CGO, and TKO Source Current | | V _{SRC} = 12V, V _{PIN} = 10V V _{CTL} = 3V (Note 5) | 3.5 | 5 | | mA |
| Under/Overvoltage to DSO, CGO, TKO Transition Delay | tv-DELAY | | 270 | 320 | 370 | ms |
| SHDN, CTL Input High (Note 6) | | Rising edge | 2.4 | | | V |
| SHDN, CTL Input Low (Note 6) | | Falling edge | | | 1.2 | V |
| SHDN, CTL Input Leakage Current | | PKN = BN | | | 1 | μΑ |
| SHDN, CTL Delay to Output Change | | | | 50 | | ns |
| DSO, CGO, TKO Output High (Note 7) | | V _{B_P} = 4V, V _{CTL} = 3V | | -0.1 | | ٧ |
| DSO, CGO, TKO Output Low (Note 7) | | V _{B_P} = 4V | | -14 | | ٧ |

ELECTRICAL CHARACTERISTICS

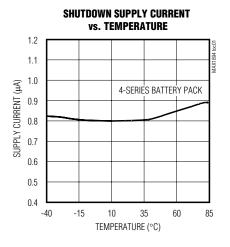
 $(V_{SRC} = V_{B4P} + 0.1V, each battery cell voltage (V_{CELL}) = 3.6V, V_{CTL} = V_{SHDN} = V_{PKN}, T_A = -40^{\circ}C to +85^{\circ}C, unless otherwise noted.)$

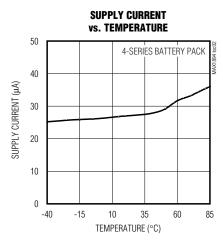
| PARAMETER | SYMBOL | CONDITIONS | MIN | TYP | MAX | UNITS | |
|--|----------------------|--|------|-----|------|-------|--|
| SRC Input Current | | V _{SRC} - V _{B_P} = 1V | | | 40 | μΑ | |
| Supply Current (Note 1) | ISUP | No faults | | | 50 | μΑ | |
| Shutdown Supply Current | ISHDN | Undervoltage without charge source | | | 2 | μΑ | |
| Charge-Mode Detection Threshold | | V _{SRC} - V _{B4P} | 25 | | 100 | mV | |
| Oversity the second second (Night and | M | MAX1894X cell voltage rising | 4.21 | | 4.29 | | |
| Overvoltage Threshold (Note 4) | Vov_th | MAX1924X, MAX1924V cell voltage rising | 4.32 | | 4.38 | V | |
| Undervoltage Threshold (Note 4) | V _{UV_TH} | Cell voltage falling | 2.24 | | 2.36 | V | |
| PKN to BN Discharge-Current Fault Threshold | V _{OD_TH} | | 120 | | 170 | mV | |
| PKN to BN Charge-Current Fault Threshold | V _{OC_TH} | | -130 | | -70 | mV | |
| PKN to BN Discharge-Current Fault Threshold, Pack Short Condition | V _{PS_TH} | | 345 | | 465 | mV | |
| Discharge- or Charge-Current Fault to DSO, CGO, TKO Transition Delay Time | t _{I-DELAY} | | 2 | | 4 | ms | |
| Discharge-Current Fault to DSO Transition Time Delay for Pack Short Condition | tp-DELAY | | 370 | | 480 | μs | |
| Charge-Voltage Comparator Threshold for Resetting Discharge-Current Fault Latch | | VSRC - VB4P | 25 | | 100 | mV | |
| Discharge-Voltage Comparator Threshold for Resetting Charge- Current Fault Latch | | V _{B4P} - V _{SRC} | 25 | | 100 | mV | |
| DSO, CGO, and TKO Sink Current | | V _{SRC} = 12V, V _{PIN} = 5V (Note 5) | 100 | | | μΑ | |
| DSO, CGO, and TKO Source Current | | V _{SRC} = 12V, V _{PIN} = 10V V _{CTL} = 3V (Note 5) | 3.5 | | | mA | |
| Under/Overvoltage to DSO, CGO, TKO Transition Delay | tv-delay | | 270 | | 370 | ms | |
| SHDN, CTL Input High (Note 6) | | Rising edge | 2.4 | | | V | |
| SHDN, CTL Input Low (Note 6) | | Falling edge | | | 1.2 | V | |

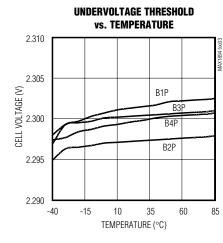
- **Note 1:** Average current from the top of the battery pack. Measured at V_{CC}.
- Note 2: Typical supply current for the top cell during the 0.5ms sampling period.
- Note 3: Input bias current for this measurement is valid when all cell voltages are equal and the measurement is made over a time greater than 3 seconds.
- Note 4: Each cell voltage is sampled individually and a differential measurement is made (V_{B4P} V_{B3P}, V_{B3P} V_{B2P}, V_{B2P} V_{B1P}, and V_{B1P} BN).
- Note 5: V_{PIN} represents V_{DSO}, V_{CGO}, or V_{TKO}.
- Note 6: Inputs to SHDN and CTL pins are referred to PKN.
- Note 7: Measurements are with respect to VSRC.

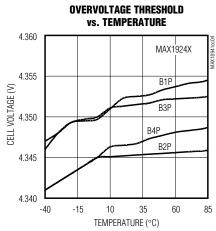
Typical Operating Characteristics

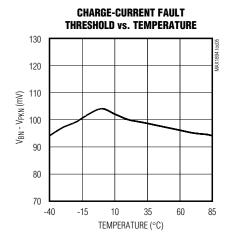
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

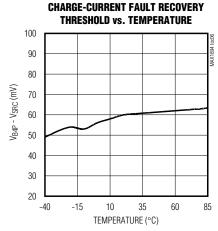


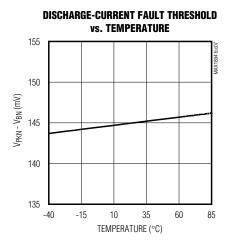


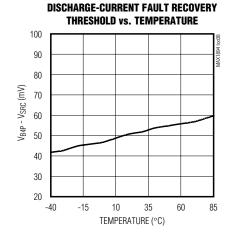


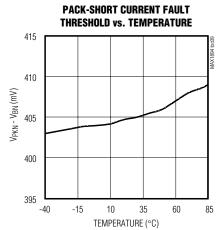






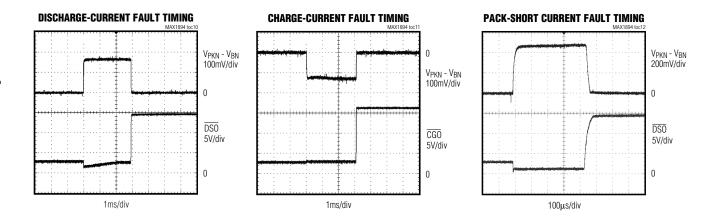






Typical Operating Characteristics (continued)

 $(T_A = +25$ °C, unless otherwise noted.)



Pin Description

| PIN | NAME | FUNCTION |
|-----|------|--|
| 1 | B4P | Cell 4 Positive Connection. Short B4P to B3P for MAX1924V. |
| 2 | Vcc | Supply Input. Connect this pin to the top of the battery pack through a diode and a capacitor (see the <i>Typical Application Circuit</i>). |
| 3 | B3P | Cell 3 Positive Connection |
| 4 | IC3 | Internal Connection. Float this pin. |
| 5 | B2P | Cell 2 Positive Connection |
| 6 | IC2 | Internal Connection. Float this pin. |
| 7 | B1P | Cell 1 Positive Connection |
| 8 | IC1 | Internal Connection. Float this pin. |
| 9 | BN | Battery Negative. Connection for the cell 1 negative terminal and the top of the current-sense resistor R _{SENSE} . BN is also chip ground. |
| 10 | PKN | Pack Negative. The sense resistor (RSENSE) is connected between BN and PKN. |
| 11 | CTL | Control Input. Drive CTL low for normal operation. Drive CTL high to turn off the three external protection MOSFETs. |
| 12 | SHDN | Shutdown. Drive SHDN low for normal operation. Drive SHDN high to put the device into shutdown if no charger is present. |
| 13 | TKO | Trickle-Charge Driver Output. TKO drives the gate of an external P-channel trickle-charge MOSFET low (on) in normal operation. |
| 14 | CGO | Fast-Charge Driver Output. CGO drives the gate of an external P-channel fast-charge MOSFET low (on) in normal operation. |
| 15 | DSO | Discharge Driver Output. DSO drives the gate of an external P-channel discharge control MOSFET low (on) in normal operation. |
| 16 | SRC | Common Source Connection for MOSFETs. SRC provides the bias for gate drivers DSO, TKO, and CGO. |

Detailed Description

The MAX1894/MAX1924 battery-pack protectors supervise the charging and discharging process of Li+ cells. Designed for 3-series (MAX1924V) and 4-series (MAX1894X/MAX1924X) applications, these devices monitor the voltage across each cell to provide protection against undervoltage, overvoltage, and overcurrent damage.

Output pins $\overline{\text{CGO}}$, $\overline{\text{TKO}}$, and $\overline{\text{DSO}}$ control external MOSFET gates. These MOSFETs, in turn, control the fast-charging, trickle-charging, and discharge processes of the battery pack (Figure 1).

Modes of Operation

Shutdown Mode

The MAX1894/MAX1924 go into shutdown mode under two conditions: the SHDN pin is driven high without a charger applied, or a battery cell undervoltage fault is detected, also without a charger applied. In shutdown mode, the device consumes 0.8µA (typ) on the VCC pin and all MOSFETs are off. The MAX1894/MAX1924 stay in shutdown mode as long as no charging voltage is applied to the battery pack (VSRC is less than the pack voltage). When the battery pack is connected to a charger (VSRC > VB4P + 0.1V) and the pack voltage is above 4.5V, the device goes into normal operating mode and begins monitoring the pack (see Figure 2).

Normal Mode

In the normal mode of operation, the MAX1894/MAX1924 are in either a standby mode ($29\mu\text{A}$ typ) or sample mode ($160\mu\text{A}$ typ). The device enters the standby mode from shutdown mode. The standby mode lasts for 79ms; then the device goes into the sample mode. During sample mode, the MAX1894/MAX1924 check each cell for overvoltage and undervoltage. Sample mode lasts for 0.5ms; then the MAX1894/MAX1924 return to standby mode. During sample mode, the MAX1894/MAX1924 do not introduce cell mismatch.

During normal mode operation, the MAX1894/MAX1924 continuously monitor the voltage across R_{SENSE} for charge or discharge current faults, or battery pack-short faults.

Protection Features

Overvoltage Protection

The MAX1894/MAX1924 provide overvoltage protection to avoid overcharging cells. When an overvoltage fault is detected in four consecutive samples, \overline{CGO} and \overline{TKO} go high, stopping the charging process. The MAX1894/MAX1924 continue to sample the cell voltages, and if no overvoltage is detected, \overline{CGO} and \overline{TKO}

Table 1. Flow Chart Symbol Table

| SYMBOL | DESCRIPTION |
|---------------------|---|
| V _{OC} _TH | Charge-Current Fault Threshold (Negative Value) |
| V _{OD_TH} | Discharge-Current Fault Threshold |
| V _{PS_TH} | Pack-Short Discharge-Current Fault Threshold |
| V _{UV_TH} | Undervoltage Threshold |
| Vov_th | Overvoltage Threshold |
| Vsrc | MOSFET Common Source Voltage |
| VRSENSE | Sense Resistor Voltage |
| Vov_hyt | Overvoltage Threshold Hysteresis |
| OVF | Overvoltage Sample Counter |
| UVF | Undervoltage Sample Counter |

are returned to the normal low state (see Figure 3). The MAX1924 also includes a hysteresis of 200mV.

The overvoltage threshold is preprogrammed and requires no external components. The overvoltage threshold is factory set at 4.25V (typ) for the MAX1894 and 4.35V (typ) for the MAX1924. Contact Maxim for more information on threshold levels between 4V and 4.4V.

Undervoltage Protection

The MAX1894/MAX1924 provide undervoltage protection to avoid overdischarging the cells. With no battery charger present, and an undervoltage fault is detected in four consecutive samples, \overline{DSO} , \overline{CGO} , and \overline{TKO} go high and the device goes into shutdown mode (see Figure 4).

If a battery charger is applied to the battery pack and one or more cells are below V_{UV_TH} , then only \overline{TKO} goes low, allowing trickle-charge current to flow. If no undervoltage is detected in any sample, \overline{DSO} , \overline{CGO} , and \overline{TKO} all go low.

The undervoltage threshold is preprogrammed at 2.30V (typ). Contact Maxim for more information on threshold levels between 2V and 3.2V.

Charge-Current Fault Protection

The MAX1894/MAX1924 protect against excessive charge current by monitoring the voltage developed across RSENSE. RSENSE is connected between BN and PKN. If VRSENSE exceeds the charge-current fault threshold (VOC_TH, typically 100mV) for more than 3ms, the charge current comparator is tripped, setting \overline{CGO} and \overline{TKO} high.

The charge-current fault condition is latched and is not reset until the MAX1894/MAX1924 detect a reversal in

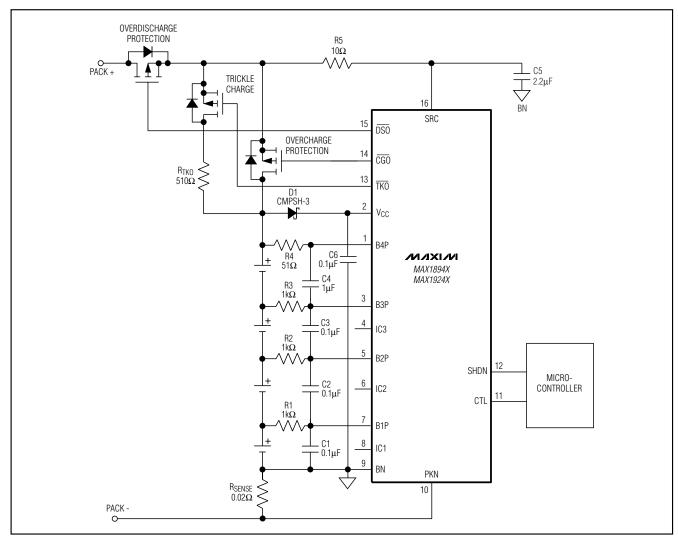


Figure 1. Typical Applications Circuit with Trickle Charge

the direction of current flow. To reverse the current flow, the charger has to be removed (Figure 5). The sustaining condition for the latch is a 100mV (max) voltage drop across SRC and B4P. Since the charge-current fault threshold between BN and PKN is also 100mV (typ), the RDS_ON of the overcharge protection MOSFET must be greater than the sense resistor in order to ensure a latched state.

Discharge-Current Fault Protection

The MAX1894/MAX1924 protect against excessive discharge-current by monitoring the voltage developed across R_{SENSE}. If V_{RSENSE} exceeds the discharge-current fault threshold (V_{OD TH}, typically 145mV) for more

than 3ms, the discharge-current comparator is tripped, setting $\overline{\text{DSO}}, \overline{\text{CGO}},$ and $\overline{\text{TKO}}$ high.

Discharge-current fault is latched and is not reset until the MAX1894/MAX1924 detect a reversal in the direction of current flow. To reverse the current flow, a charger must be applied (Figure 6).

Pack-Short Current Fault Protection

The MAX1894/MAX1924 protect against a shorted pack by monitoring the voltage developed across RSENSE. If VRSENSE exceeds the pack-short threshold (VPS_TH, typically 405mV) for more than $\frac{450\mu s}{CGO}$, $\frac{1}{DSO}$, and $\frac{1}{TKO}$ high.

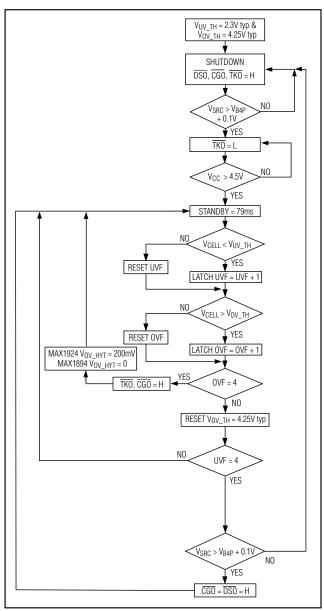


Figure 2. Undervoltage and Overvoltage Protection Flow Chart

Pack-short current fault is latched and is not reset until the MAX1894/MAX1924 detect a reversal in the direction of current flow. A charger must be applied to reverse the current flow (Figure 7).

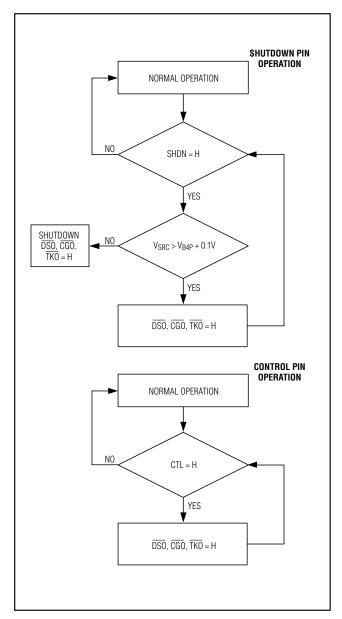


Figure 3. Shutdown and Control Pin Flow Charts

_Design Procedure

Fast and Trickle-Charge Paths

The MAX1894/MAX1924 offer the designer the flexibility of two charging paths: a fast charging path and a trickle-charge path (see Figure 1). Trickle charging is enabled and $\overline{\text{TKO}}$ is set low when one or more cells are belows VUV_TH.

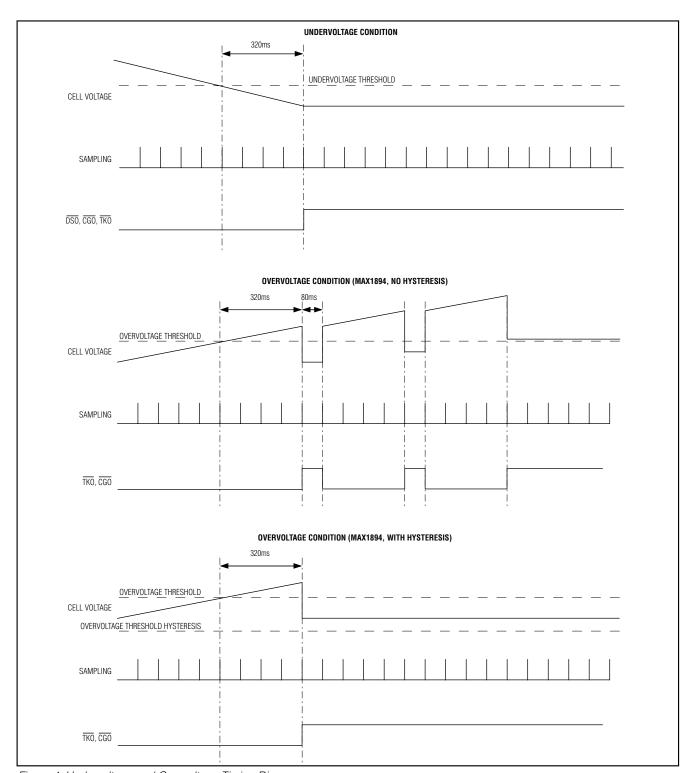


Figure 4. Undervoltage and Overvoltage Timing Diagrams

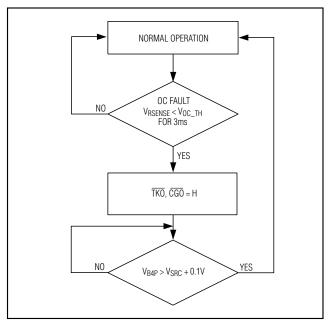


Figure 5. Charge-Current Fault

Set the nominal values of the trickle charge current by selecting resistor R_{TKO} based on the following equation:

where V_{CHRG} is the charger output voltage, V_{PACK} is the battery-pack voltage, and $I_{\overline{1}KO}$ is the trickle-charge current.

When the trickle-charge option is not used, float $\overline{\text{CGO}}$ and connect $\overline{\text{TKO}}$ to the gate of the overcharge protection MOSFET (see Figure 9). When a charger is applied and the voltage on one or more cells is less than VUV_TH, the MAX1894/MAX1924 modulate the $\overline{\text{TKO}}$ output until all cells exceed VUV_TH.

Protection FET Drivers

All three external MOSFETs have their source pins connected to the SRC pin. When a MOSFET is turned off, FET drivers pull the gate to the SRC voltage. Additional external pullup resistors are not needed. When the MOSFET is turned on, the VGS is limited to -14V by a clamp circuit built in the drivers. This allows use of MOSFETs with maximum VGS of -20V. All three drivers have the same circuitry and drive capability. The quiescent current in normal operation is less than 3µA per driver.

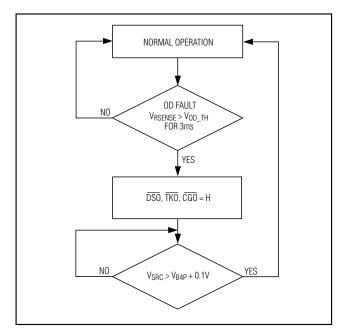


Figure 6. Discharge-Current Fault

RSENSE Selection

All current faults are detected using a current-sense resistor connected between BN and PKN. The value of this resistor sets the fault current levels. Charge-current fault is given by:

$$I_{OC_TH} = \frac{V_{OC_TH}}{R_{SENSE}} = \frac{100mV}{R_{SENSE}}$$

Discharge-current fault is given by:

$$I_{OD_TH} = \frac{V_{OC_TH}}{R_{SENSE}} = \frac{145mV}{R_{SENSE}}$$

Pack-short current fault is given by:

$$I_{PS_TH} = \frac{V_{PS_TH}}{R_{SENSE}} = \frac{405mV}{R_{SENSE}}$$

Select Rsense to obtain the desired fault current levels. For example, a $20m\Omega$ Rsense sets the charge current fault at 5A. Choose an Rsense that can withstand the dissipation during normal operation and current fault conditions. For example, pack-short current is given by:

Table 2. State Table

| STATE | CTL STATE | SHDN STATE | CHARGER APPLIED | GOES INTO SHUTDOWN MODE | TKO | CGO | DSO |
|--|-----------|---------------|--------------------|----------------------------|-----|-----|-----|
| Undervoltage | L | L | Yes | No | L | Н | Н |
| Undervoltage | L | L | No | Yes | Н | Н | Н |
| Overvoltage | L | L | Х | No | Н | Н | L |
| Charge Current Fault | L | L | Yes | No | Н | Н | L |
| Discharge Current Fault | L | L | No | No | Н | Н | Н |
| Pack Short Current Fault | L | L | No | No | Н | Н | Н |
| Forced Shutdown by | Х | Н | No | Yes | Н | Н | Н |
| External µP | Х | Н | Yes | No | Н | Н | Н |
| CTL | Н | L | Х | No | Н | Н | Н |
| Deep Discharge (V _{CC} < 4.5V) | L | L | Yes | No | L | Н | Н |
| Normal Operation | L | L | Х | No | L | L | L |

X: Don't care.

$$I_{PS} = \frac{V_{CELL} \times N_S}{R_{DSON_DSO} + R_{DSON_CGO} + R_{SENSE} + R_{CELL} \times \frac{N_S}{N_P}}$$

where Ns is the number of cells in series, Np is number of cells in parallel, and VCELL is the cell voltage. Dissipation during pack-short current fault condition is given by:

$$P_{PS} = (I_{PS})^2 \times R_{SENSE}$$

The Rsense chosen should be able to withstand Pps dissipation. Verify power dissipation in normal operation and other current fault conditions as well.

Choosing External MOSFETs

The external P-channel MOSFETs act as switches to enable or disable charging and discharging of batteries. Different P-channel MOSFETs may be selected depending on the charge and discharge currents anticipated. In most applications, the requirements for fast-charge and discharge MOSFETs are similar and the same type of MOSFETs can be used. The trickle-charge MOSFET can be a small-signal type to minimize cost.

The MAX1894/MAX1924 MOSFET drivers have a V_{GS} clamp of -14V typical and MOSFETs with maximum V_{GS} of -20V can be used. MOSFETs must have a V_{DS} greater than the maximum pack voltage.

The power dissipation in the MOSFETs is given by:

$$P = I^2 R_{DSON}$$

The MOSFET should be chosen to withstand power dissipation during normal operation and all current fault conditions. Additional MOSFETs can be added in parallel to help these requirements. Table 3 lists some suitable MOSFETs in a small SO-8 package.

Decoupling Considerations

The MAX1894/MAX1924 must have a reliable V_{CC} bias to function properly. A severe overload, such as a short circuit at the pack terminals, can collapse the battery-pack voltage below the V_{CC} undervoltage lockout threshold. The use of a diode-capacitor peak detector on the V_{CC} input ensures continued operation during voltage transients on the battery (Figure 1). Since the MAX1894/MAX1924 typically consume only 30 μ A, D1 and C6 can be small, low-cost components. A 30V Schottky diode with a few mA current capability and a 0.1 μ F capacitor are sufficient.

The MAX1894/MAX1924 continuously monitor the differential voltage between the B4P and SRC inputs to detect the application of a charger. RC filters with similar time constants must be added to both inputs to ensure the differential voltage is not corrupted by noise.

Table 3. MOSFET Selection

| P-CHANNEL MOSFETS | MAXIMUM DRAIN CURRENT (A) |
|----------------------|------------------------------|
| IRF7404 | 6.7 |
| IRF7406 | 5.8 |
| Si4431 | 5.8 |
| Si4947 (dual) | 3.5 EA |

Protecting and Filtering Cell Inputs

Resistors in series with each B_P pin are recommended to limit the current in case there is a short between adjacent B_P pins (see Figure 1).

The intermediate cell input bias current is typically 0.5nA. A 1k Ω resistor in series with any intermediate cell moves the overvoltage trip point by typically 0.5mV, which is insignificant compared to the ± 25 mV tolerance in the overvoltage threshold. The top cell input bias current during sampling period is typically 60 μ A. To reduce the voltage change on the top cell input due to sampling current, a filter resistance of 10 Ω to 50 Ω should be added in series with the top cell. To attain the desired filter characteristics, the capacitance across the two top cell input pins should be 1 μ F.

The MAX1894/MAX1924 have internal ESD diodes on each B_P pin for ESD protection up to 2kV. When higher ESD ratings are needed, capacitors (typically 0.1µF) can be added across adjacent B_P pins (see Figure 1). The RC filters improve the device immunity to ESD and filter the noise spikes on B1P-B4P to prevent the MAX1894/MAX1924 from being triggered and latched prematurely by noise spikes.

Control Pins SHDN and CTL

SHDN and CTL allow external logic or microprocessors to control the MAX1894/MAX1924 gate drivers. Drive CTL high to turn off the three protection MOSFETs: DSO, CGO, and TKO. Drive SHDN high to force the MAX1894/MAX1924 into shutdown mode (with no charger applied). SHDN and CTL do not affect the state machine. Toggling these two pins does not change the state or reset any fault conditions. If external control circuitry or a microprocessor is not used, connect SHDN and CTL to PKN.

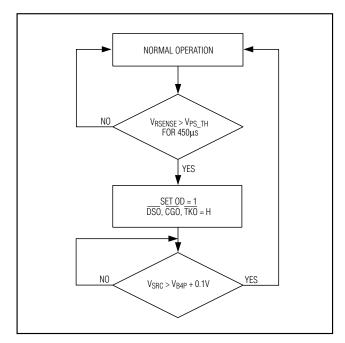


Figure 7. Pack-Short Current Fault

Layout Considerations

Good layout is important to minimize the effects of noise on the system and to ensure accurate voltage and current measurements. Use the appropriate trace widths for the high-current paths and keep traces short to minimize parasitic inductance and capacitance. Minimize current-sense resistor trace lengths and make use of Kelvin connections to the resistor. Provide adequate space and board area for the external MOSFETs and sense resistor to dissipate the heat required. Place RC filters close to B1P–B4P pins.

Chip Information

TRANSISTOR COUNT: 4259

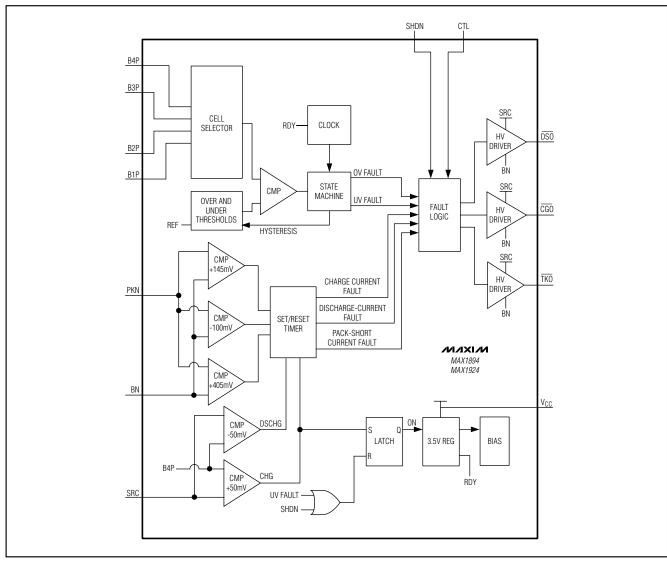


Figure 8. Simplified Functional Diagram

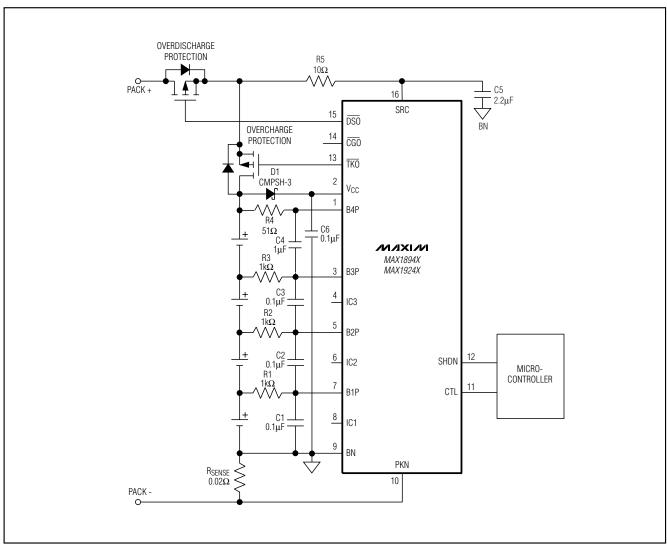
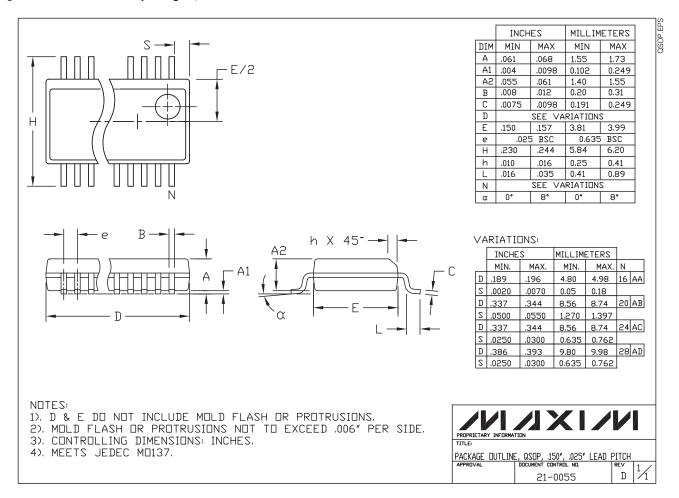


Figure 9. Typical Applications Circuit without Trickle Charge

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to **www.maxim-ic.com/packages**.)



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